MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK110E65Z

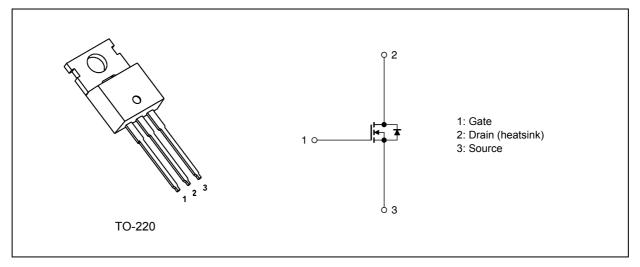
1. Applications

• Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.092 \Omega$ (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_D = 1.02 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	1
Drain current (DC)	(Note 1)	I _D	24	A
Drain current (pulsed)	(Note 1)	I _{DP}	96	1
Power dissipation $(T_c = 25 \text{ °C})$)	PD	190	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	258	mJ
Single-pulse avalanche current		I _{AS}	6	A
Reverse drain current (DC)	(Note 1)	I _{DR}	24	1
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	96	1
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	7
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2022-02

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.657	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 12.7 mH, I_{AS} = 6 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 650 V, V_{GS} = 0 V	_	_	2	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.02 mA	3	—	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 12 A	_	0.092	0.11	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	2250	—	pF
Reverse transfer capacitance	C _{rss}		_	1.9	—	
Output capacitance	C _{oss}		_	54	—	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	85	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz		3.4	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	28	—	ns
Switching time (turn-on time)	t _{on}		_	52	_	
Switching time (fall time)	t _f			4	_	
Switching time (turn-off time)	t _{off}			90	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{(BR)DSS}, \ I_D \leq 12 \ A$	90	—	_	V/ns

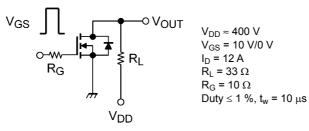


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 24 A		40	_	nC
Gate-source charge 1	Q _{gs1}		_	13	_	
Gate-drain charge	Q _{gd}			11	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 24 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	V _{DD} = 400 V,	_	300	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 12 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	_	3.9	_	μC
Peak reverse recovery current	I _{rr}		_	26	_	А
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 12$ A, V_{GS} = 0 V	40		_	V/ns

7. Marking

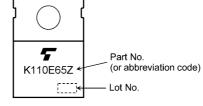
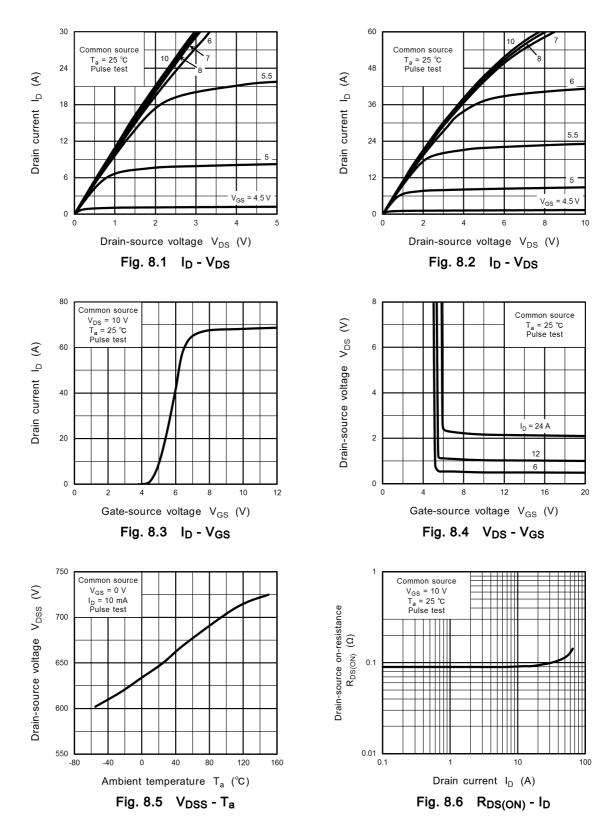
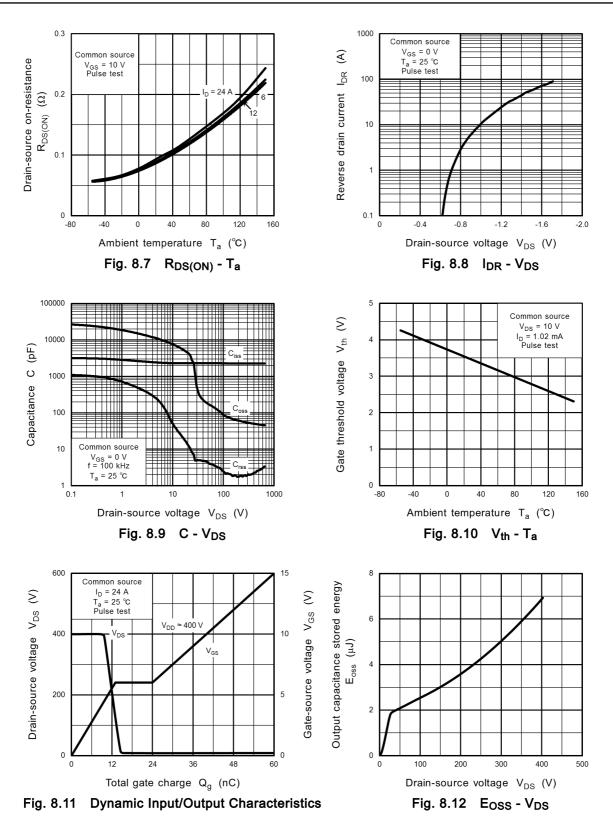


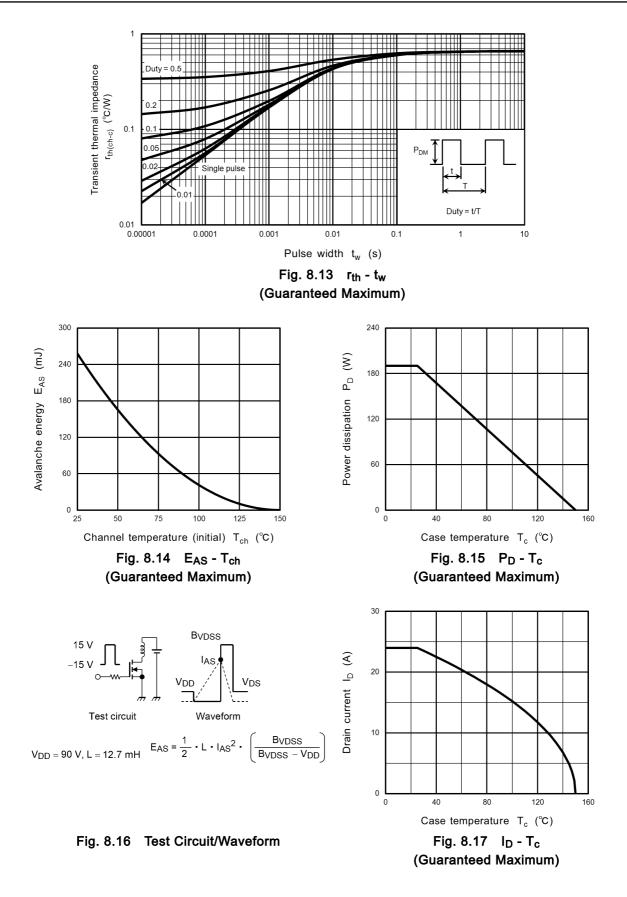
Fig. 7.1 Marking

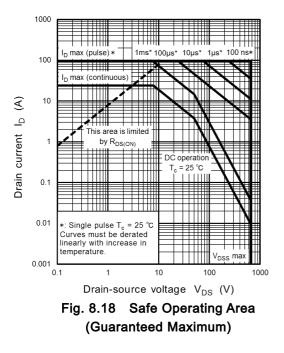
8. Characteristics Curves (Note)









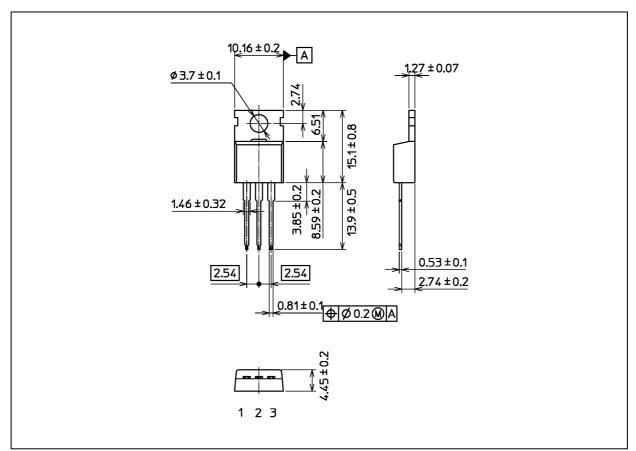


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK110E65Z

Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	

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